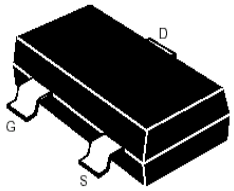
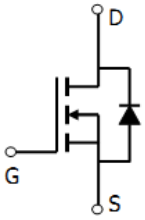
SOT-23





Features

- Advanced trench process technology
- High Density Cell Design For Ultra Low On-Resistance

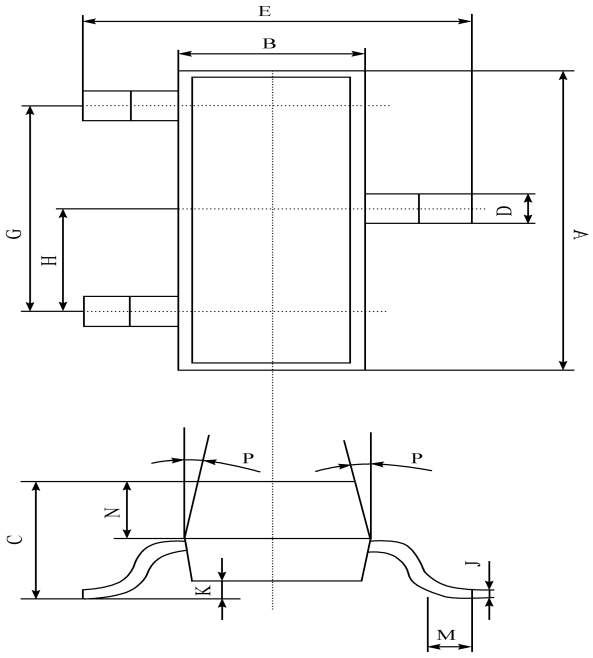
MAXIMUM RANTINGS

Characteristic	Symbol	Max	Unit
Drain-Source Voltage	BV_{DSS}	100	V
Gate- Source Voltage	V_{GS}	±20	V
Drain Current (continuous)	I_D	1.5	A
Drain Current (pulsed)	I_{DM}	6	A
Total Device Dissipation T_A=25℃	P_D	1250	mW
Junction	T_J	150	℃
Storage Temperature	T_{stg}	-55to+150	℃

Electrical Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage (I_D = -250uA,V_{GS}=0V)	BV_{DSS}	100	—	—	V
Gate Threshold Voltage (I_D = -250uA,V_{GS}= V_{DS})	$V_{GS(th)}$	1	—	3	V
Diode Forward Voltage Drop (I_S= 1 A,V_{GS}=0V)	V_{SD}	—	—	1.2	V
Zero Gate Voltage Drain Current (V_{GS}=0V, V_{DS}= 30V)	I_{DSS}	—	—	1	uA
Gate Body Leakage (V_{GS}=±20V, V_{DS}=0V)	I_{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance (I_D= 1.5A,V_{GS}= 10 V)	$R_{DS(ON)}$	—	230	270	mΩ
Static Drain-Source On-State Resistance (I_D= 1 A,V_{GS}= 4.5 V)	$R_{DS(ON)}$	—	275	340	mΩ
Input Capacitance (V_{GS}=10V, V_{DS}= 15 V,f=1MHz)	C_{ISS}	—	326	—	pF
Output Capacitance (V_{GS}=10V, V_{DS}= 15 V,f=1MHz)	C_{OSS}	—	38	—	pF
Turn-ON Time (V_{DS}= 50 V, I_D= 10 A, R_{GEN}=6Ω)	$t_{(on)}$	—	10	—	ns
Turn-OFF Time (V_{DS}= 50 V, I_D= 10 A, R_{GEN}=6Ω)	$t_{(off)}$	—	30	—	ns

SOT-23 PACKAGE OUTLINE Plastic surface mounted package



SOT-23	
A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.2
N	0.60±0.10
P	7±2°

(UNIT)：mm